

APPLICATION NO. 10/822,669

SUITE 700

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PAPER NUMBER

LICATION NO.		FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/822,669		04/13/2004	Se-young Jang	1572.1252	4799
21171	7590	01/26/2006		EXAM	NER
STAAS &	HALSE	EY LLP	DOAN, THERESA T		

2814 DATE MAILED: 01/26/2006

ART UNIT

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
	10/822,669	JANG ET AL.				
Office Action Summary	Examiner	Art Unit				
	Theresa T. Doan	2814				
The MAILING DATE of this communication app Period for Reply A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING D Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication If NO period for reply is specified above, the maximum statutory period of - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status	Y IS SET TO EXPIRE <u>03</u> MONTH ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tim will apply and will expire SIX (6) MONTHS from , cause the application to become ABANDONED	(S) OR THIRTY (30) DAYS, I. ely filed the mailing date of this communication. D (35 U.S.C. § 133).				
1) Responsive to communication(s) filed on	_·					
2a) ☐ This action is FINAL . 2b) ☑ This	action is non-final.					
3) Since this application is in condition for allowa	nce except for formal matters, pro	secution as to the merits is				
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims						
 4) Claim(s) 1-14 is/are pending in the application 4a) Of the above claim(s) is/are withdrays. 5) Claim(s) is/are allowed. 6) Claim(s) 1-14 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or 	wn from consideration.					
Application Papers						
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) accomposed and all accomposed and all accomposed and accomposed accomposed and accomposed and accomposed and accomposed a	epted or b) objected to by the Eddrawing(s) be held in abeyance. See ition is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CFR 1.121(d).				
Priority under 35 U.S.C. § 119						
 12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Burea * See the attached detailed Office action for a list 	s have been received. s have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National Stage				
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 04/13/04.	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:					

DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-3 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shi et al. (U.S. 6,746,896) in view of Admitted Prior Art (APA).

Regarding claim 1, Shi (Fig. 2) discloses a method of surface-mounting semiconductor chips on a PCB, including mounting a flip chip type semiconductor chip on the PCB comprising: forming a solder bump on a conductive contact area of each semiconductor chip on a back of a semiconductor wafer 100 mounted with a plurality of semiconductor chips (Fig. 2, column 5, lines 6-9); injecting underfill material on the area of the semiconductor wafer 100 formed with the solder bump 110 (Fig. 2, column 5, lines 9-16); hardening the underfill material partially to have a cohesive property (column 5, lines 15-16 and lines 33-67); severing the semiconductor wafer into the plurality of the semiconductor chips (column 5, lines 20-30); arranging the severed semiconductor chips having the hardened underfill material on the PCB (Fig. 2, column 5, lines 29-32); and heating the PCB at a predetermined temperature (column 5, lines 33-36).

Shi (Fig. 2) discloses a method of surface-mounting semiconductor chips on a PCB, including mounting a flip chip type semiconductor chip on the PCB, but fails to disclose a flip chip type semiconductor chip on the PCB mounted with electronic components.

However, APA (Fig. 2) shows that a PCB 400 is mounted with a semiconductor chip 200 and other electronic components 300 (see Background of the invention, paragraph [0007], lines 2-4) for a design choice dependent on the fabrication process being employed. Accordingly, it would have been obvious to one having ordinary skill in the art at the time of the invention was made to modify the process of forming the device of Shi by forming a flip chip type semiconductor chip on the PCB mounted with electronic components for a design choice dependent on the fabrication process being employed, as taught by APA.

Regarding claim 2, Shi discloses that the predetermined heating temperature is above the temperature of a melting point of the solder bump (column 6, lines 8-11).

Regarding claim 3, Shi (Fig. 2) discloses that the underfill material is solidified during the heating (column 5, lines 15-16).

3. Claims 4-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shi et al. (U.S. 6,746,896) in view of Farnworth (U.S. 6,881,607).

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Regarding claim 4, Shi (Fig. 2) discloses a process of preparing a wafer to be used for surface mounting a semiconductor chip on a PCB comprising: forming a plurality of solder balls 110 on a surface of a semiconductor wafer 100 (Fig. 2, column 5, lines 6-9); coating the surface of the semiconductor wafer formed with the solder balls 110 with underfill material (column 5, lines 9-16); curing the underfill material (column 5, lines 33-67).

Shi does not disclose a step of curing the underfill material to achieve a semisolid state.

However, Farnworth (Figs. 9-11) teaches a method for underfilling and encapsulating flip-chip configured semiconductor device mounted on a carrier substrate to form semisolid dam structure of photopolymeric material to entrap liquid (see Abstract) by using the laser light beam 112 to cure liquid resin 60 to at least a semisolid state for adjusting the size (column 14, lines 42-45). Accordingly, it would have been obvious to one having ordinary skill in the art at the time of the invention was made to modify the process of Shi by performing a step of curing the underfill material to achieve a semisolid state because such curing the underfill material would achieve a semisolid state for adjusting the size, as taught by Farnworth (column 14, lines 42-45).

Regarding claim 5, Shi discloses that a temperature to cure the underfill material to a semisolid state is lower than a reflow temperature of the solder balls (column 6, lines 8-11).

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Regarding claim 6, Shi (Fig. 2) discloses further comprising: severing the semiconductor wafer into the plurality of the semiconductor chips (column 5, lines 20-30); arranging the plurality of semiconductor chips on the PCB (column 5, lines 29-32); and raising the temperature of the PCB to a predetermined temperature (column 5, lines 33-36).

Regarding claims 7 and 12, Shi discloses that the predetermined temperature is above the reflow temperature of the solder balls (column 6, lines 8-11).

Regarding claim 8, Shi discloses that the underfill is cured to a solid state at the predetermined temperature (column 5, lines 45-59).

Regarding claim 9, Shi discloses that the height of the underfill coating is approximately equal to the height of the solder balls (column 5, lines 16-19).

Regarding claim 10, Farnworth (Fig. 11) discloses that the height of the underfill coating 60 is above the height of the solder balls 30.

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Regarding claims 11-14, Shi (Fig. 2) discloses a process of surface mounting flip chip type semiconductor chips on a PCB comprising: forming a plurality of solder bumps 110 on a surface of a flip chip type semiconductor wafer (column 5, lines 6-9); injecting the surface of the flip chip type semiconductor wafer 100 formed with solder bumps 110 with underfill material to a height approximately equal to the solder bumps (Fig. 2, column 5, lines 9-19); curing the underfill material (column 5, lines 33-67); severing the flip chip type semiconductor wafer 100 into a plurality of flip chip semiconductor chips (column 5, lines 20-30); arranging the plurality of flip chip semiconductor chips on the PCB (Fig. 2, column 5, lines 29-32); and raising the temperature of the PCB to a predetermined temperature (column 5, lines 33-34).

Shi does not disclose a step of curing the underfill material to achieve a semisolid state.

However, Farnworth (Figs. 9-11) teaches a method for underfilling and encapsulating flip-chip configured semiconductor device mounted on a carrier substrate to form semisolid dam structure of photopolymeric material to entrap liquid (see Abstract) by using the laser light beam 112 to cure liquid resin 60 to at least a semisolid state for adjusting the size (column 14, lines 42-45). Accordingly, it would have been obvious to one having ordinary skill in the art at the time of the invention was made to modify the process of Shi by performing a step of curing the underfill material to achieve a semisolid state because such curing the underfill material would achieve a semisolid state for adjusting the size, as taught by Farnworth (column 14, lines 42-45).

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Conclusion

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Theresa T. Doan whose telephone number is (571) 272-1704. The examiner can normally be reached on Monday to Friday from 7:00AM - 4:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, WAEL FAHMY can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Theresa Doan

January 20, 2006